

KSC5345

High Voltage and High Reliability

- High speed Switching
- Wide Safe Operating Area



1.Base 2.Collector 3.Emitter

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	900	V
V_{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	14	V
I _C	Collector Current (DC)	5	Α
I _{CP}	*Collector Current (Pulse)	10	Α
I _B	Base Current (DC)	2	Α
I _{BP}	*Base Current (Pulse)	4	Α
P _C	Power Dissipation(T _C =25°C)	40	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

^{*} Pulse Test: Pulse Width = 5ms, Duty Cycle≤10%

Thermal Characteristics $\rm T_{C}\text{=}25^{\circ}C$ unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	1.25	°C/W
$R_{\theta ja}$		Junction to Ambient	62.5	

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$\textbf{Electrical Characteristics} \ \, \textbf{T}_{\text{C}} = 25 \, ^{\circ} \text{C unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 500\mu A, I_E = 0$	900	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	450	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	14	-	-	V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 800 \text{ V}, I_{E} = 0$	-	-	10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 14V, I_{C} = 0$	-	-	10	μА
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$	15	-		
h_{FE2}		$V_{CE} = 5V, I_{C} = 3A$	8	-		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$	-	-	1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$	-	-	1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, f = 1MHz$	-	65		pF
f _T	Current Gain bandwidth Product	$V_{CE} = 10V, I_{C} = 0.6A$	-	14	-	MHz
t _{STG}	Storage Time	$V_{CC} = 125V, I_{C} = 1A$		-	6.5	μs
t _F	Fall Time	$I_{B1} = -I_{B2} = 0.2A$	-	-	0.3	
t _{STG}	Storage Time	$V_{CC} = 250V, I_{C} = 4A$	-	-	3	μs
t _F	Fall Time	$I_{B1} = 0.8A, I_{B2} = -1.6A$	-	-	0.3	

Typical Characteristics

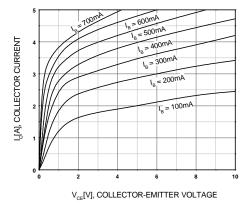


Figure 1. Static Characteristic

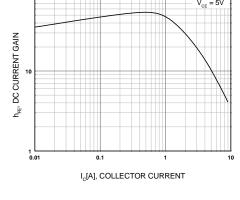


Figure 2. DC current Gain

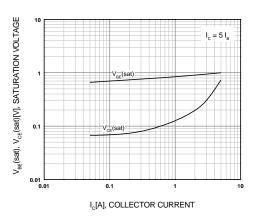


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

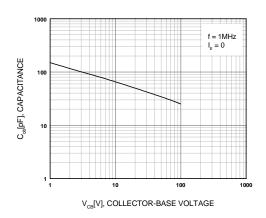


Figure 4. Collector Output Capacitance

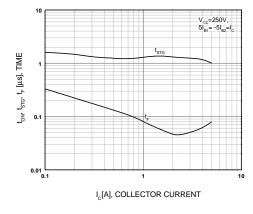


Figure 5. Switching Time

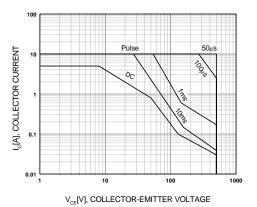


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

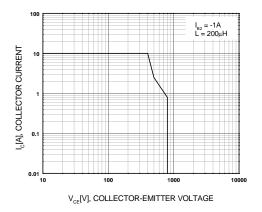


Figure 7. Reverse Bias Safe Operating Area

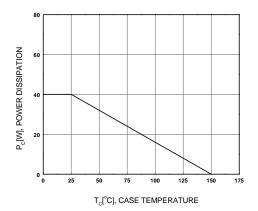
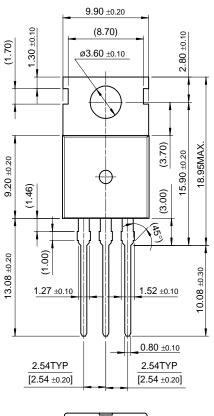
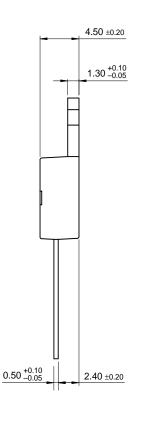


Figure 8. Power Derating

TO-220





10.00 ±0.20

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